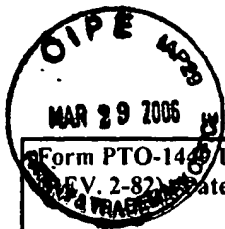


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Form PTO-1449 U.S. Department of Commerce
REV. 2-82 Patent and Trademark OfficeAtty. Docket No.
A35760-PCT-USA
(070050.2713)Serial No.
10/525,288INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(Use several sheets if necessary)

Applicant
James S. ImFiling Date
02/16/2005Group
2813Examiner
Rodgers

U.S. PATENT DOCUMENTS

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
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Collier et al.

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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
<i>CR</i>	80.	6621044	09/01/2003	Jain et al.
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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
<i>CR</i>	96.	6582827	06/24/2003	Im
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*Colleen E. Goff*Date Considered *23 March 2007*

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	Examiner <i>Rodgers</i>	

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					Yes	No
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<i>CR</i>	112.	9824118	06/04/1998	WO		

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Exam Initial	No.	Document No.	Publication Date	Country	Translation	
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<i>CR</i>	113.	9931719	06/24/1999	WO		<u>No</u>
<i>CR</i>	114.	0014784	03/16/2000	WO		
<i>CR</i>	115.	0118854	03/15/2001	WO		
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Exam Initial	No.	Document No.	Publication Date	Country	Translation	
					Yes	No
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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
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Examiner

Colleen J. Rodgers

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23 March 2007

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